

**FORM PTO 444** U.S. Department of Commerce  
Patent and Trademark Office

List of Documents Cited by Applicant

Application No.:	10/550,040
Filing Date:	September 21, 2005
First Named Inventor:	Johnson et al.
Group:	Unassigned
Examiner:	Unassigned
Attorney Docket No.:	297/171 PCT/US

U.S. PATENT DOCUMENTS

Examiner Initial	Cite No.	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, where relevant passages or relevant figures appear
	1	6,756,795	06/29/2004	Hunt et al.	
	2	6,693,327	02/17/2004	Priefert et al.	
	3	2004/0029365	02/12/2004	Linthicum et al.	
	4	2004/0029365	02/12/2004	Linthicum et al.	
	5	6,686,261	02/03/2004	Gehrke et al.	
	6	2003/0230235	12/18/2003	Craven et al.	
	7	6,657,305	12/2/2003	Cohen et al.	
	8	6,645,295	11/11/2003	Koike et al.	
	9	2003/0207551	11/06/2003	Gehrke et al.	
	10	2003/0194828	10/16/2003	Zheleva et al.	
	11	6,627,974	09/30/2003	Kozaki et al.	
	12	2003/0198301	08/23/2003	Terashima et al.	
	13	6,608,327	08/19/2003	Davis et al.	
	14	6,602,763	08/05/2003	Davis et al.	
	15	6,582,986	07/24/2003	Kong et al.	
	16	2003/0139037	07/24/2003	Kobayashi et al.	
	12	2003/0111008	08/19/2003	Strittmatter et al.	
	18	2003/0070607	04/17/2003	Koike et al.	

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /B.K./

	19	6,534,332	03/18/2003	Bourret-Courchesne	
	20	6,521,514	2/18/2003	Gehrke et al.	
	21	6,506,660	01/14/2003	Holmes et al.	
	22	2002/0179911	12/05/2002	Linthicum et al.	
	23	2002/0180306	12/05/2002	Hunt et al.	
	24	6,478,871	11/12/2002	Shealy et al.	
	25	6,462,355	10/08/2002	Linthicum et al.	
	26	6,429,463	08/06/2002	Mauk	
	27	6,423,475	07/23/2002	Lyons et al.	
	28	6,376,339	04/23/2002	Linthicum et al.	
	29	2002/0014629	02/7/2002	Shibata et al.	
	30	2001/0040292	11/15/2001	Hahn et al.	
	31	2001/0041427	11/15/2001	Gehrke et al.	
	32	2001/0039102	11/08/2001	Zheleva et al.	
	33	6,265,298	07/24/2001	Chen et al.	
	34	2001/0008299	07/19/2001	Linthicum et al.	
	35	6,255,198	07/03/2001	Linthicum et al.	
	36	6,184,144	02/06/2001	Lo	
	37	6,177,688	01/23/2001	Linthicum et al.	
	38	6,160,833	12/12/2000	Floyd et al.	
	39	6,153,010	11/28/2000	Kiyoku et al.	
	40	6,111,276	08/29/2000	Mauk	
	41	6,090,685	07/18/2000	Gonzales et al.	
	42	6,051,849	04/18/2000	Davis et al.	
	43	5,962,863	10/05/1999	Russell et al.	
	44	5,865,888	02/02/1999	Min et al.	

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /B.K./

	45	4,803,181	02/07/1989	Buchmann et al.	
	46	4,760,036	07/26/1988	Schubert	
	47	4,758,528	07/19/1988	Goth et al.	
	48	4,354,896	10/19/1982	Hunter et al.	

## FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number (country code, no., kind code (if known))	Publication Date	Name of Patentee or Applicant	Pages, columns, lines where relevant passages appear	T

## OTHER DOCUMENTS

Examiner Initials	Cite No.	Include Author (in CAPITAL LETTERS), Title, Journal, Date, Pertinent Pages, Etc.	T
	49	International Preliminary Examination Report for PCT/US04/08725 dated February 9, 2006.	
	50	International Preliminary Examination Report for PCT/US04/08725 dated November 25, 2005	
	51	BERGER ET AL., "Liquid Phase Epitaxial Growth of Silicon on Porous Silicon for Photovoltaic Applications", <i>Cryst. Res. Technol.</i> , Vol. 36, pp. 1005-1010 (2001)	
	52	Z.R. ZYTKIEWICZ, "Epitaxial Lateral Overgrowth of GaAs: Principle and Growth Mechanism", <i>Cryst. Res. Technol.</i> , Vol. 34, pp. 573-582 (1999)	
	53	<a href="http://semiconductorglossary.com/default.asp?searchterm=ELO">http://semiconductorglossary.com/default.asp?searchterm=ELO</a> ; (publication date unknown)	
	54	BASHIR ET AL., "Characterization of Sidewall Defects in Selective Epitaxial Growth of Silicon", <i>J. Vac. Sci. Technol.</i> , pp. 923-927 (May/June 1995)	
	55	JU ET AL., "Epitaxial Lateral Overgrowth of Gallium Nitride on Silicon Substrate", Department of Chemical Engineering and Condensed Matter and Surface Science Program, Ohio University, pp. 1-9, (Publication Date Unknown)	
	56	TAKENAKA ET AL., "0.15 $\mu$ m T-shaped Gate Fabrication for GaAs MODFET Using Phase Shift Lithography", <i>IEEE Transactions on Electron Devices</i> , Vol. 43, No. 2 (February 1996)	
	57	STICKEL ET AL., "Edge Contrast: A New Definition for Comparative Lithography Tool Characterization", <i>J. Vac. Sci. Technol.</i> , pp.1007-1010 (Oct-Dec. 1983)	

58	BARATTE ET AL., "Enhance/Deplete GaAs Sisfets", IEEE pp.121-135 (1987)	
59	CHOI ET AL., "A Spacer Patterning Technology for Nanoscale CMOS", <i>IEEE Transactions on Electron Devices</i> , Vol. 49, No. 3 (March 2002)	
60	CHOI ET AL., "Sub-20nm CMOS FinFET Technologies", Department of Electrical Engineering and Computer Sciences, University of California, pp. 19.1.1-19.1.4 (Publication Date Unknown)	
61	CHOI ET AL., "Nanoscale CMOS Spacer FinFET for the Terabit Era", <i>IEEE Electron Device Letters</i> , Vol. 23, No. 1 (January 2002)	
62	CHOI ET AL., "Spacer FinFET: Nano-scale CMOS Technology for the Terabit Era", Department of Electrical Engineering and Computer Science, University of California, pp. 543-546 (Publication date unknown)	
63	ZHANG ET AL., "A Lithography Independent Gate Definition Technology for Fabricating Sub-100nm Devices", Institute of Microelectronics, Peking University, pp. 81-84 (2001)	
64	STOLK ET AL., "Making 50 nm Transistors with 248 nm Lithography", <i>2000 Symposium on VLSI Technology Digest Technical Papers</i> , pp. 52-53 (2000)	
65	NASRULLAH ET AL., "An Edge-Defined Nano-Lithography Technique Suitable for Low Thermal Budge Process and 3-D Stackable Devices", <i>IEEE</i> , pp. 502-505 (2003)	
66	CHUNG ET AL., "Deep-Submicrometer MOS Device Fabrication Using a Photoresist-Ashing Technique", <i>IEEE Electron Device Letters</i> , Vol. 9, No. 4 (April 1988)	
67	STRIFLER ET AL., "An Edge-Defined Technique for Fabricating Submicron Metal-Semiconductor Field Effect Transistor Gates", <i>J. Vac. Sci. Technol.</i> , pp. 1297-1299 (Nov/Dec 1990)	
68	HOSACK ET AL., "Submicron Patterning of Surfaces", <i>IEEE Journal of Solid-State Circuits</i> , Vol. SC-12, No. 4 (August 1997)	
69	ZHELEVA ET AL., "Pendeo-Epitaxy – A New Approach for Lateral Growth of Gallium Nitride Structures", pp. 81-84 (Publication date unknown)	

EXAMINER /Brook Kebede/ DATE CONSIDERED 05/02/2008

\*Examiner Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.